

SUPPORT FOR THE AMENDMENTS

Newly-added Claims 7 and 8 are supported by the specification and original claims. Accordingly, no new matter is believed to have been added to the present application by the amendments submitted above.

REMARKS

Claims 1-8 are pending. Favorable reconsideration is respectfully requested.

The present invention relates to a process for producing a carbon-containing SiO<sub>2</sub>-containing insulating layer on chips, wherein at least one silicon compound selected from the group consisting of (1) alkylarylalkoxysilanes, (2) arylalkoxysilanes, (3) C<sub>1</sub>- and C<sub>3</sub>-C<sub>5</sub> alkyl orthosilicates, (4) orthosilicates having glycol radicals, (5) orthosilicates having polyether radicals, (6) hydrogenalkoxysilanes, (7) hydrogenaryloxysilanes, (8) alkyl-hydrogensilanes, (9) alkylhydrogenalkoxysilanes, (10) dialkylhydrogenalkoxysilanes, (11) arylhydrogensilanes, (12) arylhydrogenalkoxysilanes, (13) acetoxy silanes, (14) silazanes, (15) siloxanes, (16) organofunctional silanes bearing at least one acetoxy, azido, amino, cyano, cyanato, isocyanato or ketoximato group, (17) organofunctional silanes containing at least one heterocycle, with the silicon atom being able to belong to the heterocycle itself or be covalently bound to the heterocycle, (18) mixtures of at least two silicon compounds described above and (19) mixtures of tetraethoxysilane with at least one silicon compound described above, is used as precursor. See Claim 1.

The rejections of the claims under 35 U.S.C. §102(b) over Andidieh and under 35 U.S.C. §103(a) over Andidieh in view of Komada are respectfully traversed. The cited references fail to disclose or suggest the claimed process for producing a carbon-containing SiO<sub>2</sub>-containing insulating layer on chips.

Andidieh describes a method of forming a carbon doped oxide layer on a substrate. See the Abstract. This reference fails to disclose the use of silicon compounds (1)-(19) set forth in Claim 1 to produce a carbon-containing SiO<sub>2</sub>-containing insulating layer on chips as claimed. Komada discloses a gas barrier film. This reference also fails to disclose the use of silicon compounds (1)-(19) set forth in Claim 1 to produce a carbon-containing SiO<sub>2</sub>-containing insulating layer on chips as claimed.

In view of the foregoing, Andidieh alone or in combination with Komada fail to disclose or suggest the claimed process. Accordingly, the subject matter of the pending claims is neither anticipated by or obvious over those references. Withdrawal of this ground of rejection is respectfully requested.

The objection to the claims and the rejection of the claims under 35 U.S.C. §112, first paragraph, are believed to be obviated by the amendments submitted above.

Claim 1 has been amended to specify a process for producing a carbon-containing SiO<sub>2</sub>-containing insulating layer and the members of the Markush grouping have been clarified.

Withdrawal of the objection and this ground of rejection is respectfully requested.

Regarding the Election/Restriction, rejoinder is requested.

Applicants submit that the present application is in condition for allowance. Early notice to this effect is earnestly solicited.

Respectfully submitted,

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